Corrections to "Opportunities in Device Scaling for 3-nm Node and Beyond: FinFET Versus GAA-FET Versus UFET"

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IN THE above article [1], there was a typo in Fig. 14. The units for current density should be "J[A*cm^–2]." The corrected figure is presented here.

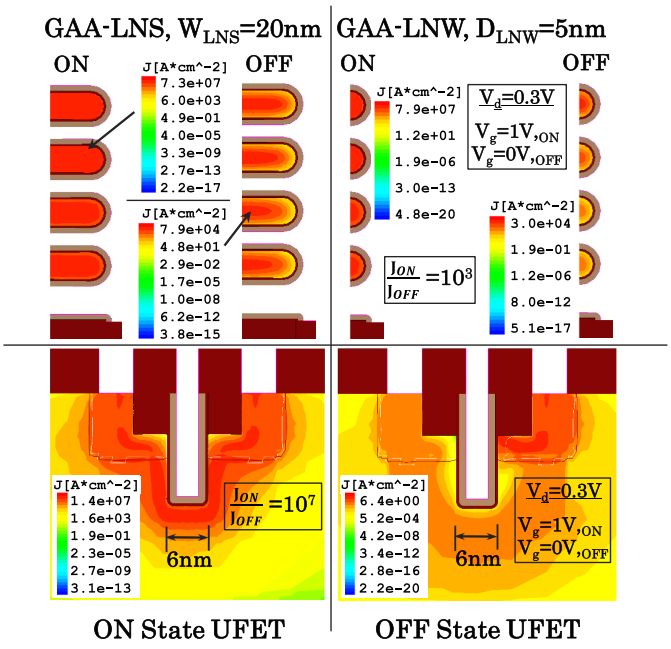

Fig. 14. Electron current density (J) in the channel regions with a minimum gate foot-print having 6 nm (UFET width is 20 nm).

REFERENCES

[1] U. K. Das and T. K. Bhattacharyya, "Opportunities in device scaling for 3-nm node and beyond: FinFET versus GAA-FET versus UFET," *IEEE Trans. Electron Devices.*, vol. 67, no. 6, pp. 2633–2638, Jun. 2020.

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